
PRODUCT CHANGE NOTICE

**Wafer Fabrication Site Change
for Intersil Product
ISL55012IEZ-T7**

**Refer to:
PCN11069**

Date: July 18, 2011

July 18, 2011

To: Our Valued Intersil Customer

Subject: **Wafer Fabrication Site Change for Intersil Product ISL55012IEZ-T7 –**
NXP Semiconductor Nijmegen, Netherlands

This notice is to inform you that Intersil has qualified the NXP Semiconductor facility in Nijmegen, The Netherlands for wafer fabrication of the ISL55012IEZ-T7 QuBiC3 technology product. The change in wafer fabrication site is necessary as the NXP facility in Fishkill, New York has discontinued manufacturing operations. The QuBiC3 technology wafer fabrication operations have been relocated from the NXP Fishkill to the NXP Nijmegen facility. The product and site-specific qualification activities are complete.

The NXP Nijmegen facility is ISO 9001:2008 and ISO/TS 16949:2002 certified. The product and site qualification plans are designed using JEDEC and other applicable industry standards to confirm there is no impact to form, fit, function, or interchangeability of the product. A summary of the qualification results is included for reference. The remainder of the manufacturing operations (package assembly, package electrical testing, shipment, etc.) will continue to be processed to previously established conditions and systems.

There will be no change to the product data sheet specification or external marking of the packaged product. Product affected by this change is identifiable via Intersil's internal traceability system.

Intersil will take all necessary actions to conform to agreed upon customer requirements and to ensure the continued high quality and reliability of Intersil products being supplied. Customers may expect to receive product from either the current or the newly qualified sites beginning ninety days from the date of this notification or earlier with approval.

If you have concerns with this change notice, Intersil must hear from you promptly. Please contact the nearest Intersil Sales Office or call the Intersil Corporate line at 1-888-468-3774, in the United States, or 1-321-724-7143 outside of the United States.

Regards,



Jon Brewster
Intersil Corporation

PCN11069

CC: J. Touvell J. McNamara J. Yun C. Ludeman P. Randhawa L. Tran

PCN11069 – ISL55012 Qualification Summary

Legend

Fail	Warning	Pass	QBE	Waived	NA
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Reliability Test	EL8200IY fab'ed using CQUBIC3 10 LEAD MSOP using SG600, CRM-1076DJ at UNM Plan Rel: 2010-08-02	ISL55012 fab'ed using CQUBIC3 6 LEAD SC-70 using SG600, A8006NS, 1 MIL GOLD wire at UNM	ISL55015 fab'ed using CQUBIC3 6 LEAD SC-70 using SG600, A8006NS, 1 MIL GOLD wire at UNM	ISL59837IAZ fab'ed using CQUBIC3 16 LEAD QSOP using SG600, A8290, 1 M GOLD wire at UNM Plan Rel: 2010-08-02	Comments
High Temperature Operating Life	SRN090285 Rev 0 0/65 125C 3000hr completed 2010-06-29 disposition=A SRN090285 Rev 1 0/65 125C 3000hr completed 2010-06-29 disposition=A SRN090285 Rev 5 0/78 125C 3000hr completed 2010-07-02 disposition=A risk release: 1000	SRN100392 Rev 0 0/70 85C 168hr completed 2010-11-03 disposition=A	SRN100392 Rev 0 0/70 85C 168hr completed 2010-11-03 disposition=A	SRN100060 Rev 1 0/78 125C 3000hr completed 2010-10-05 disposition=A	
Biased HAST	NA	NA	NA	SRN100060 Rev 0 2/78 130C, 85%RH PRECOND L2 PBFREE 96hr completed 2010-05-10 disposition=A SRN100060 Rev 1 0/50 130C, 85%RH PRECOND L2 PBFREE 96hr completed 2010-05-25 disposition=A	ISL59837IAZ : IA101803 Electrical Overstress (2 @96hr)

Reliability Test	EL8200IY fab'ed using CQUBIC3 10 LEAD MSOP using SG600, CRM- 1076DJ at UNM Plan Rel: 2010-08-02	ISL55012 fab'ed using CQUBIC3 6 LEAD SC-70 using SG600, A8006NS, 1 MIL GOLD wire at UNM	ISL55015 fab'ed using CQUBIC3 6 LEAD SC-70 using SG600, A8006NS, 1 MIL GOLD wire at UNM	ISL59837IAZ fab'ed using CQUBIC3 16 LEAD QSOP using SG600, A8290, 1 M GOLD wire at UNM Plan Rel: 2010-08-02	Comments
Storage Life	NA	NA	NA	SRN100060 Rev 1 0/78 150C BAKE AND REFLOW 1000hr completed 2010-07- 20 disposition=A	
Destructive Wire Pull after Storage Life	NA	NA	NA	SRN100060 Rev 0 0/4 completed 2010-02- 08 disposition=C	
Bond Pull Integrity	NA	NA	NA	SRN100060 Rev 0 0/0 175C 96hr completed 2010-05- 05 disposition=A SRN100060 Rev 1 0/3 175C completed 2010-02-08 disposition=A SRN100060 Rev 2 0/3 175C completed 2010-02-08 disposition=A	
Moisture Sensitivity Classification	MRT09118 MSL=2@260C (Pb Free) Approved=Yes	NA	NA	MRT10026 MSL=2@260C (Pb Free) Approved=Yes	
Unbiased HAST	SRN090285 Rev 0 0/78 130C, 85%RH PRECOND L2 PBFREE 96hr completed 2009-12-09 disposition=A	NA	NA	NA	

Reliability Test	EL8200IY fab'ed using CQUBIC3 10 LEAD MSOP using SG600, CRM-1076DJ at UNM Plan Rel: 2010-08-02	ISL55012 fab'ed using CQUBIC3 6 LEAD SC-70 using SG600, A8006NS, 1 MIL GOLD wire at UNM	ISL55015 fab'ed using CQUBIC3 6 LEAD SC-70 using SG600, A8006NS, 1 MIL GOLD wire at UNM	ISL59837IAZ fab'ed using CQUBIC3 16 LEAD QSOP using SG600, A8290, 1 M GOLD wire at UNM Plan Rel: 2010-08-02	Comments
Temperature Cycle	SRN090285 Rev 0 0/78 -65C TO 150C PRECOND L2 PBFREE 500cy completed 2009-12-11 disposition=A	NA	NA	SRN100060 Rev 0 0/78 -40C TO 125C PRECOND L2 PBFREE 1000cy completed 2010-04-27 disposition=A	
Destructive Wire Pull after Temp Cycle	NA	NA	NA	SRN100060 Rev 0 0/4 completed 2010-06-02 disposition=A	
Product Electrical Characterization	Performed by Product Engineering	Perform by Product Engineer	Perform by Product Engineer	Performed by Product Engineering	
ESD Characterization	Performed by Product Engineering HBM: 2500V MM: 400V CDM: 1000V	Perform by Product Engineer HBM = 4000V MM = 250V CDM = 2000V	Perform by Product Engineer HBM = 4000V MM = 250V CDM = 2000V	Performed by Product Engineering HBM: 2000V MM: 200V CDM: 1000V	ISL55012: QBE: Reference ISL55015
Latch-up Characterization	Performed by Product Engineering latchup Pass Class II Level A	Perform by Product Engineer Latchup Pass Class II Level A	Perform by Product Engineer Latchup Pass Class II Level A	Performed by Product Engineering Latchup Pass Class II Level A	ISL55012: QBE: Reference ISL55015